

Walid Ouerghui

List of Publications by Year in descending order

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16
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#	ARTICLE	IF	CITATIONS
1	Spin-orbit coupling effect on electronic, linear and nonlinear optical properties of Bi ₂ S ₃ and the ternary bismuth sulfide Bi ₂ S _{2.75} Se _{0.25} : Ab-initio calculations. <i>Optical and Quantum Electronics</i> , 2022, 54, 1.	3.3	10
2	DFT calculations on ZnO _{1-x} compounds for optoelectronic applications. <i>Journal of Computational Electronics</i> , 2021, 20, 467-479.	2.5	8
3	DFT calculations of optoelectronic properties of cubic $\text{In}_{1-x}\text{Al}_x$. <i>Journal of Computational Electronics</i> , 2021, 20, 467-479.	2.5	8
4	Optical properties of quaternary GaMnAsP thin layer grown by molecular beam epitaxy. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2021, 131, 114733.	2.7	6
5	Hybrid functional calculations of electro-optical properties of novel Ga _{1-x} In _x Te ternary chalcogenides. <i>Applied Physics A: Materials Science and Processing</i> , 2020, 126, 1.	2.3	8
6	Density functional investigation of structural, electronic, optical and thermodynamic properties of Zn _{1-x} BexO semiconductor. <i>Applied Physics A: Materials Science and Processing</i> , 2019, 125, 1.	2.3	10
7	Ab Initio Study of Structural, Electronic, and Magnetic Properties of A _{1-x} III _x . <i>Journal of Superconductivity and Novel Magnetism</i> , 2018, 31, 2089-2097.	1.8	6
8	Circularly Polarized Emission from Ensembles of InGaAs/GaAs Quantum Rings. <i>Silicon</i> , 2017, 9, 689-693.	3.3	0
9	First-principles calculations on magnetism and exchange interactions in GaMnAs and GaMnAsP. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1700115.	1.5	9
10	Annealing effect on the magnetization reversal and Curie temperature in a GaMnAs layer. <i>Journal of Magnetism and Magnetic Materials</i> , 2013, 342, 149-151.	2.3	5
11	Temperature dependent optical properties of stacked InGaAs/GaAs quantum rings. <i>Materials Science and Engineering C</i> , 2008, 28, 887-890.	7.3	1
12	Effect of carrier transfer on the PL intensity in self-assembled In (Ga) As/GaAs quantum rings. <i>EPJ Applied Physics</i> , 2006, 35, 159-163.	0.7	10
13	Size filtering effect in vertical stacks of In(Ga)As/GaAs self-assembled quantum rings. <i>Materials Science and Engineering C</i> , 2006, 26, 297-299.	7.3	2
14	Lateral carrier tunnelling in stacked In(Ga)As/GaAs quantum rings. <i>European Physical Journal B</i> , 2006, 54, 217-223.	1.5	13
15	Optical anisotropy and photoluminescence excitation density dependence for auto-organized Al _{0.28} In _{0.72} As/Al _{0.28} Ga _{0.72} As quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005, 27, 369-373.	2.7	0
16	Dependence on temperature of homogeneous broadening of InGaAs/InAs/GaAs quantum dot fundamental transitions. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005, 28, 519-524.	2.7	18